What is claimed is:

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- 1. A chemical vapor deposition method, comprising:
- (i) depositing a silicide on a substrate; and
- 5 (ii) purging residual gases remaining from said depositing step by using air including H₂O gas.
 - 2. The method as recited in claim 1, wherein in (i), said silicide is deposited using tungsten hexafluoride (WF₆) and dichlorosilane (DCS) as reaction gases.
 - 3. The method as recited in claim 1, wherein in (i), said silicide is deposited at a pressure in the range of approximately 0.1Torr to approximately 760Torr and a temperature in the range of approximately 500°C to approximately 800°C.
 - 4. The method as recited in claim 1, wherein in (ii), said air including H_2O gas further includes O_2 gas and at least one inert gas.
- 5. The method as recited in claim 4, wherein said at least one inert gas is selected from the group consisting essentially of argon (Ar), nitrogen (N₂), and helium (He).

- 6. The method as recited in claim 4, wherein a partial pressure of each of said O_2 gas and said H_2O gas is approximately 10% or more.
- 7. The method as recited in claim 1, wherein the method further comprises:
 - after (ii), purging said residual gases by successively flowing O_2 gas and at least one inert gas.
- 8. The method as recited in claim 1, wherein in (ii), said purging of said
 residual gases is carried out at a pressure in the range of approximately 500Torr to
 approximately 760Torr.
 - 9. A chemical vapor deposition method, comprising:
 - (i) loading a substrate in a load-lock chamber of a CVD system;
 - (ii) transferring said substrate into a processing chamber;
 - (iii) depositing a silicide on said substrate in said processing chamber,
 - (iv) transferring said substrate into said load-lock chamber; and
 - (v) purging residual gases remaining from said depositing step by flowing air including H₂O (g) into said load-lock chamber.

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10. The method as recited in claim 9, wherein in (iii), WF₆ and DCS are introduced as reaction gases into said processing chamber.

- 11. The method as recited in claim 9, wherein in (v), said air including H₂O gas further includes O₂ gas and at least one inert gas.
- 12. The method as recited in claim 11, wherein a partial pressure of each of said O_2 gas and said H_2O gas is 10% or more.
 - 13. The method as recited in claim 9, wherein in (v), said purging of said residual gases is carried out at a pressure in the range of approximately 500Torr to approximately 760Torr.

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- 14. The method as recited in claim 9, the method further comprising: after (v), purging said residual gases by successively flowing O_2 gas and at least one inert gas.
- - a load-lock chamber;
 - a processing chamber mounted on said load-lock chamber;
 - a vent line connected with said load-lock chamber; and
 - an air purge line connected with said load-lock chamber, wherein said air
- 20 purge line supplies air including H₂O gas.
 - 16. The apparatus as recited in claim 15, wherein said air purge line and said vent line are connected to each other.

- 17. The apparatus as recited in claim 16, further comprising a vacuum pump connected to said vent line.
- 18. The apparatus as recited in claim 15, further comprising an O_2 gas line connected to said air purge line.
 - 19. The apparatus as recited in claim 15, further comprising a filter connected to said air purge line.

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20. The apparatus as recited in claim 15, further comprising a vacuum pump connected to said air purge line.